

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSII<sup>5</sup>)

# 2SK1489

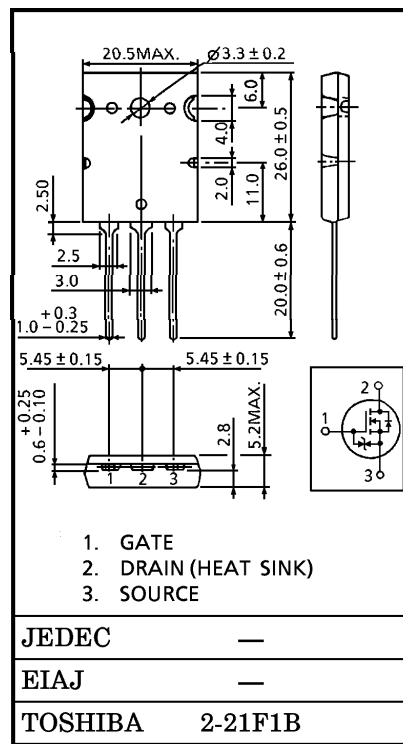
CHOPPER REGULATOR APPLICATIONS  
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

INDUSTRIAL APPLICATIONS  
Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)}=0.8\Omega$  (Typ.)
- High Forward Transfer Admittance:  $|Y_{fs}|=6.0S$  (Typ.)
- Low Leakage Current :  $I_{DSS}=300\mu A$  (Max.) ( $V_{DS}=800V$ )
- Enhancement-Mode :  $V_{th}=1.5\sim 3.5V$  ( $V_{DS}=10V, I_D=1mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		$V_{DSS}$	1000	V
Drain-Gate Voltage ( $R_{GS}=20k\Omega$ )		$V_{DGR}$	1000	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	DC	$I_D$	12	A
	Pulse	$I_{DP}$	36	
Drain Power Dissipation ( $T_c=25^\circ C$ )		$P_D$	200	W
Channel Temperature		$T_{ch}$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	$-55\sim 150$	$^\circ C$



Weight : 9.75g

THEMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.625	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	35.7	$^\circ C / W$

**This transistor is an electrostatic sensitive device.  
Please handle with caution.**

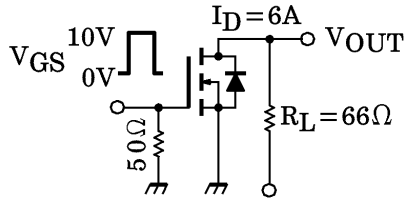
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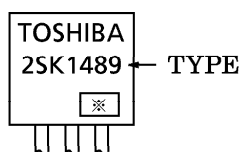
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 25V, V_{DS} = 0V$	—	—	$\pm 100$	nA
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 800V, V_{GS} = 0V$	—	—	300	$\mu A$
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	1000	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 6A$	—	0.8	1.0	$\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 6A$	4.0	6.0	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	2000	—	pF
Reverse Transfer Capacitance		$C_{rss}$		—	220	—	
Output Capacitance		$C_{oss}$		—	360	—	
Switching Time	Rise Time	$t_r$	 <p><math>I_D = 6A</math>  <math>V_{GS} = 10V, 0V</math>  <math>50\Omega</math>  <math>R_L = 66\Omega</math>  <math>V_{DD} \doteq 400V</math></p>	—	100	—	ns
	Turn-on Time	$t_{on}$		—	140	—	
	Fall Time	$t_f$		—	150	—	
	Turn-off Time	$t_{off}$		$V_{IN} : t_r, t_f < 5ns, Duty \leq 1\%, t_w = 10\mu s$	—	500	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} \doteq 400V, V_{GS} = 10V, I_D = 12A$	—	110	—	nC
Gate-Source Charge		$Q_{gs}$		—	50	—	
Gate-Drain ("Miller") Charge		$Q_{gd}$		—	60	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	12	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	36	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 12A, V_{GS} = 0V$	—	—	-1.6	V

MARKING



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)

